

Receiving Dual-Band Mixer

Description

The CXG1081TN is a receiving dual-band mixer MMIC. This IC is designed using the Sony's GaAs J-FET process.

Features

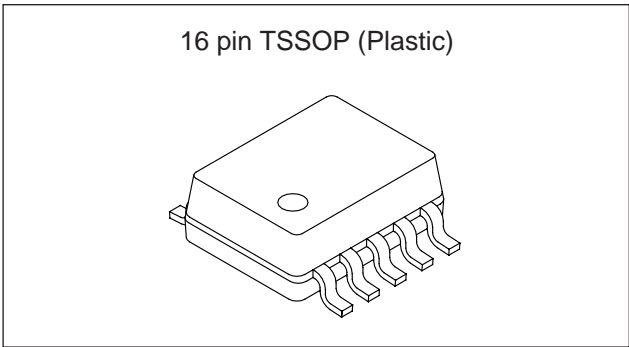
- High conversion gain  $G_c = 9.5$  to  $10.0$ dB (Typ.)
- Low noise figure  $NF = 4.4$ dB (Typ.)
- Single 2.7V power supply operation
- Low LO input power operation  $PLO = -15$ dBm
- Single CTL pin achieved by the built-in inverter circuit
- 10-pin small package

Applications

800MHz Japan digital cellular telephones (PDC)

Structure

GaAs J-FET MMIC



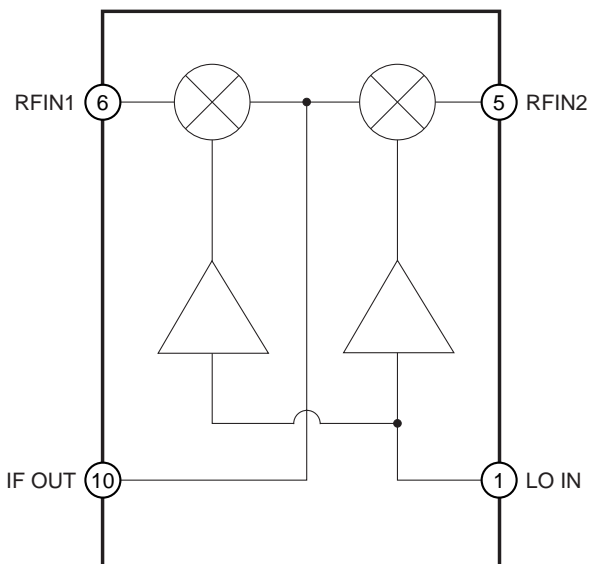
Absolute Maximum Ratings (Ta = 25°C)

• Supply voltage	V <sub>DD</sub>	4.5	V
• Input power	P <sub>IN</sub>	+5	dBm
• Current consumption	I <sub>DD</sub> (Mixer block)	15	mA
• Operating temperature	T <sub>opr</sub>	-35 to +85	°C
• Storage temperature	T <sub>stg</sub>	-65 to +150	°C

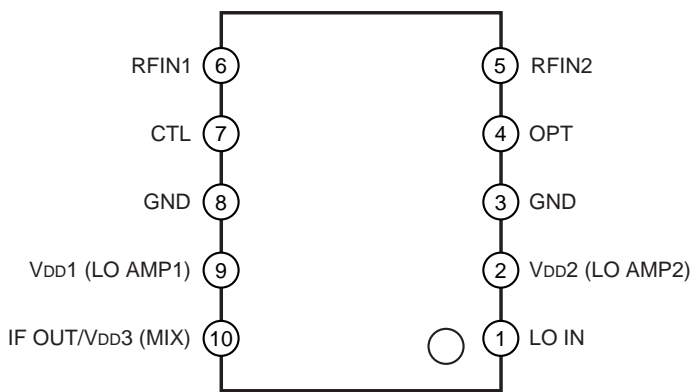
Recommended Operating Conditions

• Supply voltage	V <sub>DD</sub>	2.7 to 3.3	V
• Control voltage	V <sub>CTL</sub> (H)	2.4 to 3.3	V
	V <sub>CTL</sub> (L)	0 to 0.3	V

Block Diagram



Pin Configuration



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**Electrical Characteristics**

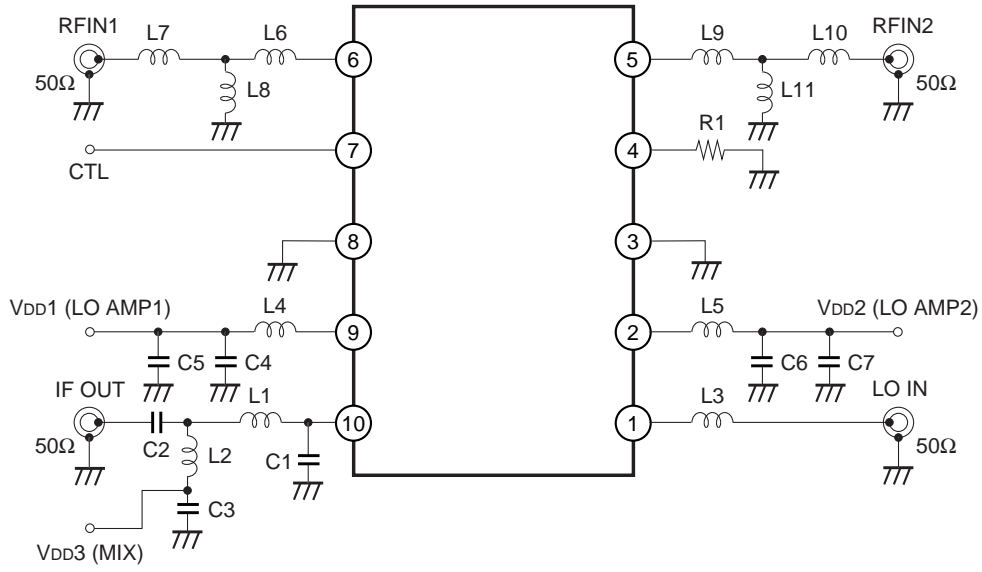
Conditions:  $V_{DD} = 2.7V$ ,  $V_{CTL} (H) = 2.7V$ ,  $V_{CTL} (L) = 0V$ ,  $f_{RF1} = 870MHz$ ,  $f_{RF2} = 820MHz$ ,  
 $f_{LO} = f_{RF} - 130MHz$ ,  $P_{LO} = -15dBm$ , unless otherwise specified

( $T_a = 25^{\circ}C$ )

Item	Symbol	Path	$V_{CTL}$	Min.	Typ.	Max.	Unit	Measurement condition	
Current consumption	$I_{DD}$	$V_{DD1}, V_{DD2}$ $V_{DD3} \rightarrow GND$	H	—	5.7	7.3	mA	When no signal	
			L						
Control current	$I_{CTL}$	CTL $\rightarrow$ GND	H	—	35	70	$\mu A$		
		CTL $\rightarrow$ GND	L	-1	0	—			
Conversion gain	$G_c$	$RF_{IN1} \rightarrow IF_{OUT}$	H	8	9.5	11.5	dB	When a small signal	
			L	—	-19	-12			
		$RF_{IN2} \rightarrow IF_{OUT}$	H	—	-21	-14			
			L	8	10	11.5			
Noise figure	NF	$RF_{IN1} \rightarrow IF_{OUT}$	H	—	4.4	6.5	dB		
		$RF_{IN2} \rightarrow IF_{OUT}$	L	—	4.4	6.5			
Input IP3	IIP3	$RF_{IN1} \rightarrow IF_{OUT}$	H	-3	-0.5	—	dBm		$P_{RF} = -25dBm$ , offset = 100kHz Conversion by the IM3 suppression ratio for two-wave input
		$RF_{IN2} \rightarrow IF_{OUT}$	L	-2.5	0	—			
LO to RF leak level	$P_{LK}$	$LO_{IN} \rightarrow RF_{IN1}$	H	—	-30	-23	dBm	$f_{LO} = 740MHz$	
		$LO_{IN} \rightarrow RF_{IN2}$	L	—	-29	-23		$f_{LO} = 690MHz$	

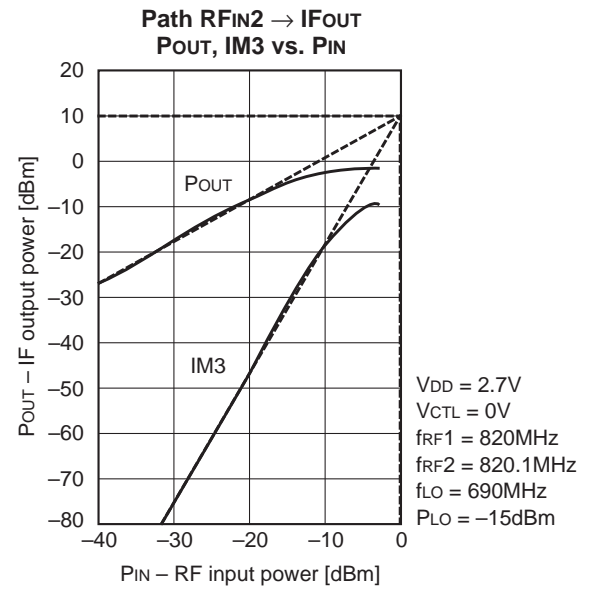
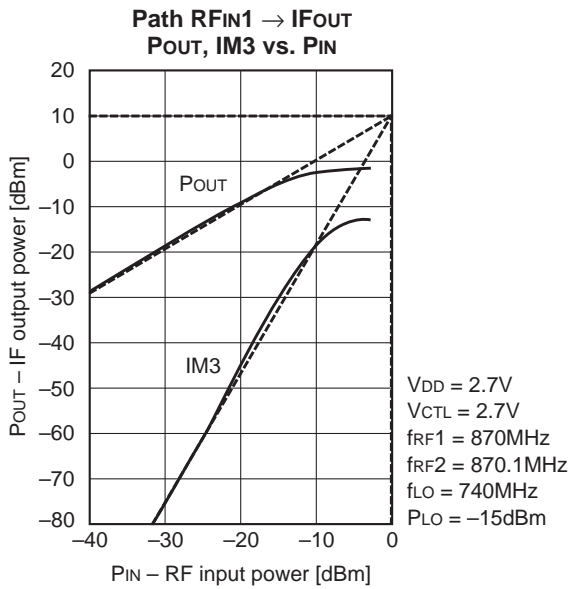
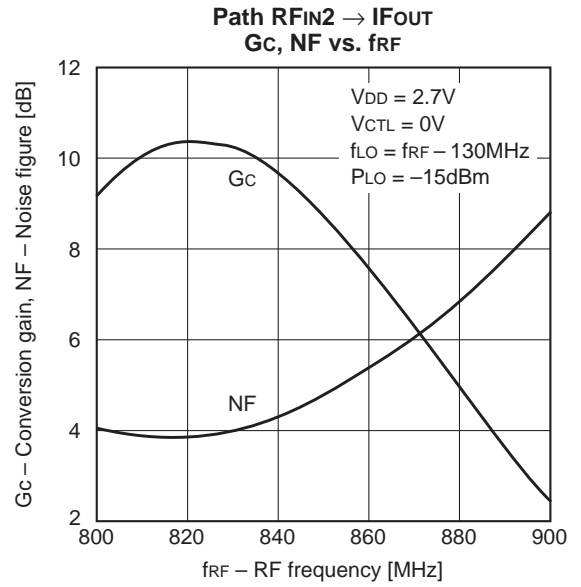
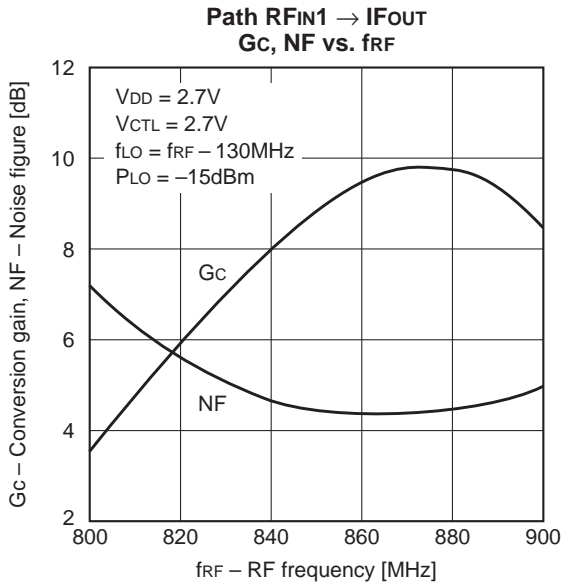
**Note)** The values shown above are the specified values on the Sony's recommended evaluation board.

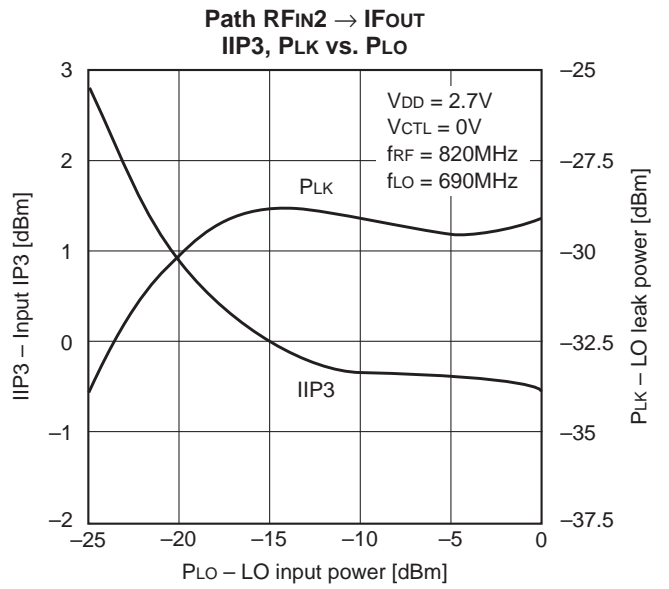
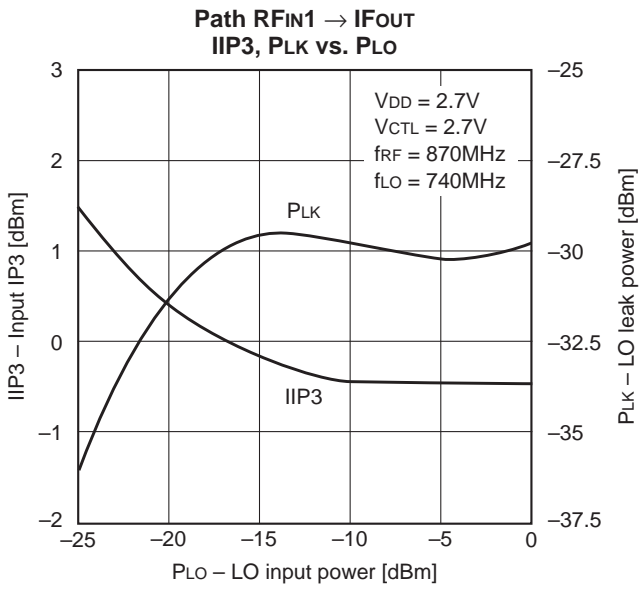
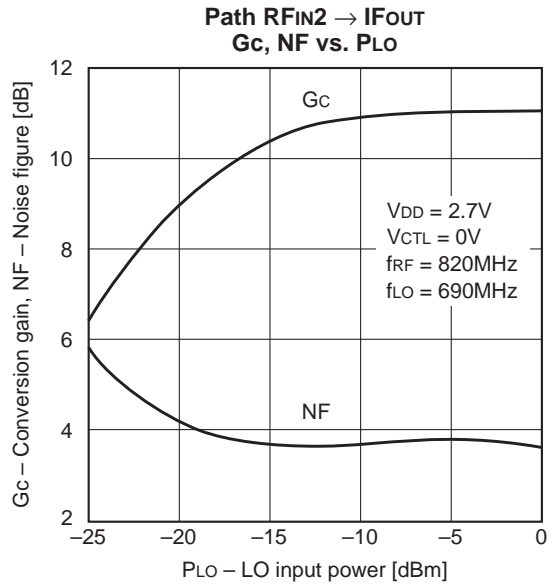
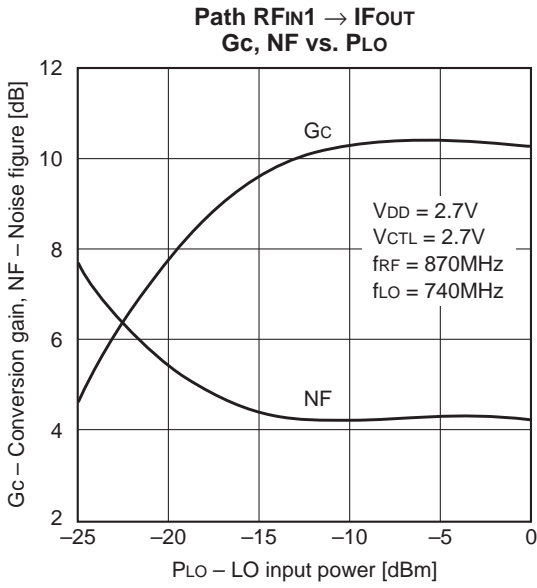
Recommended Evaluation Circuit



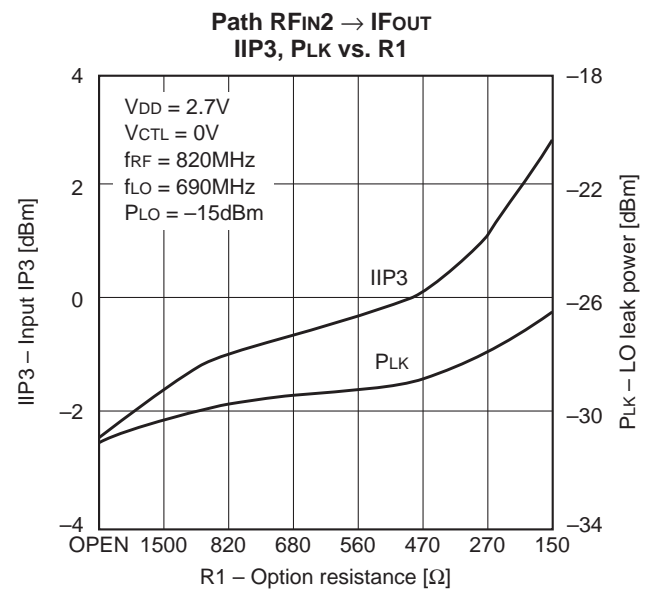
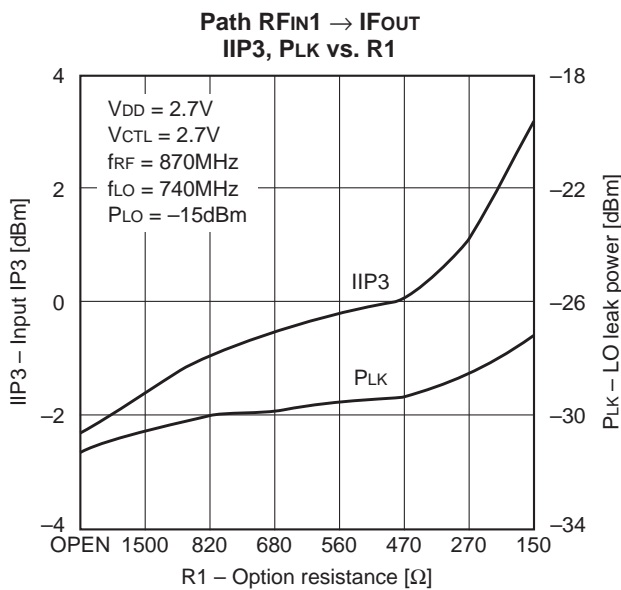
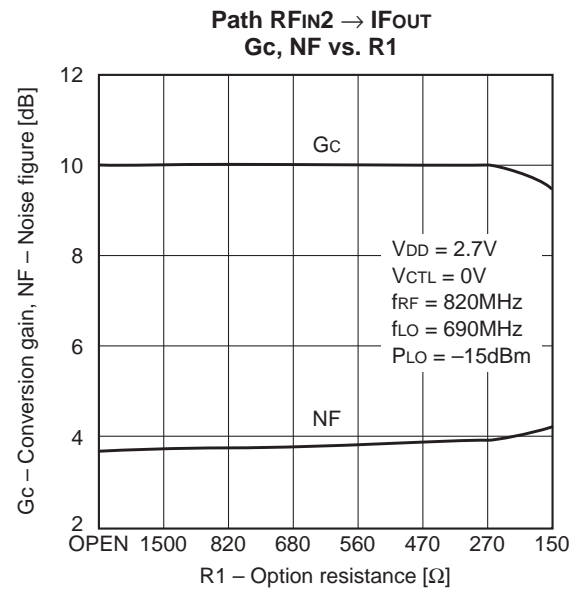
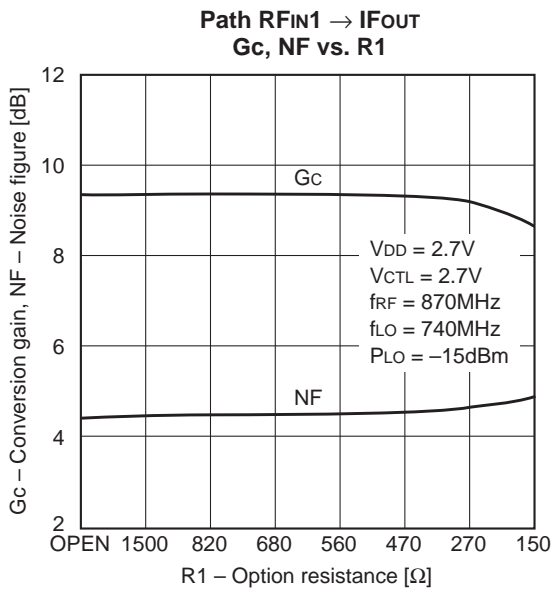
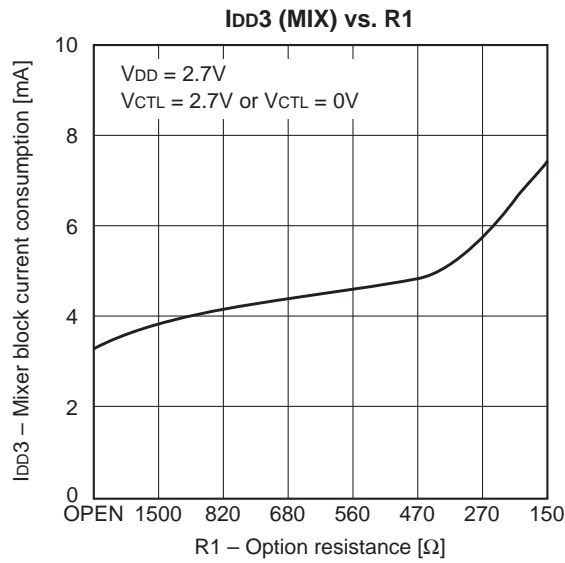
L1	82nH	L11	15nH
L2	39nH	C1	11pF
L3	27nH	C2	1000pF
L4	33nH	C3	1000pF
L5	39nH	C4	100pF
L6	27nH	C5	1000pF
L7	15nH	C6	100pF
L8	18nH	C7	1000pF
L9	33nH	R1	470Ω
L10	8.2nH		

Example of Representative Characteristics (Ta = 25°C)

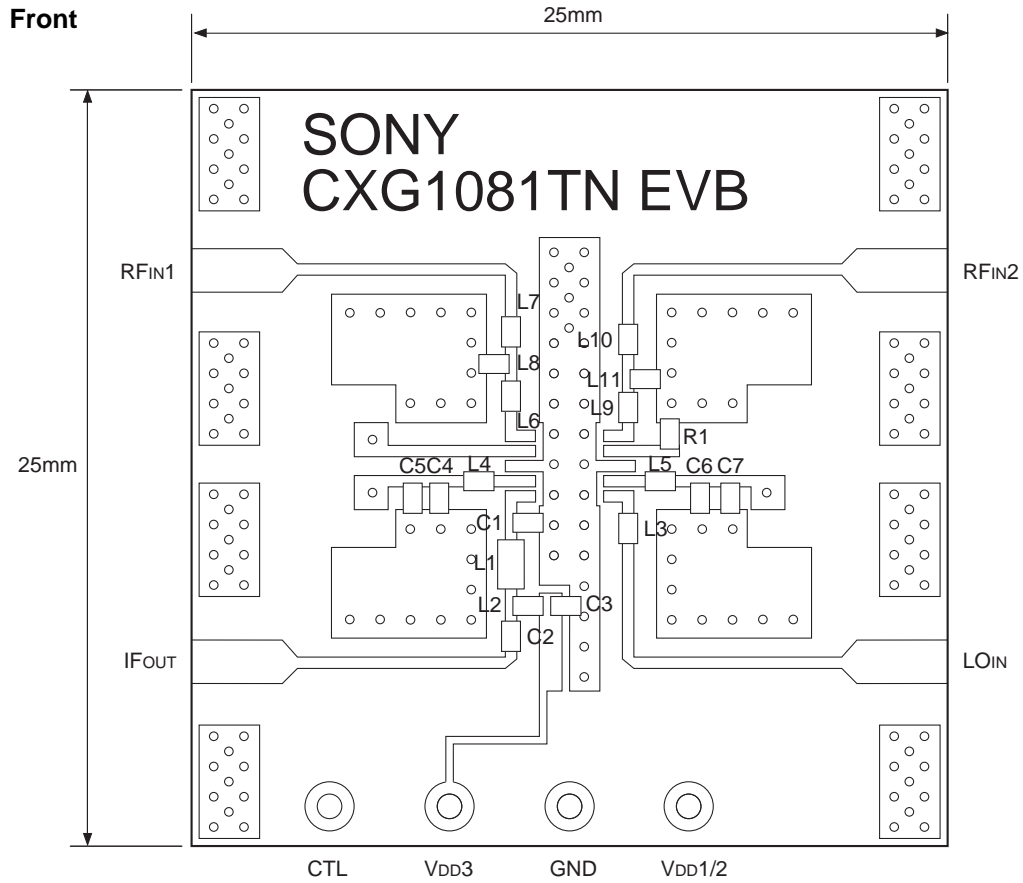




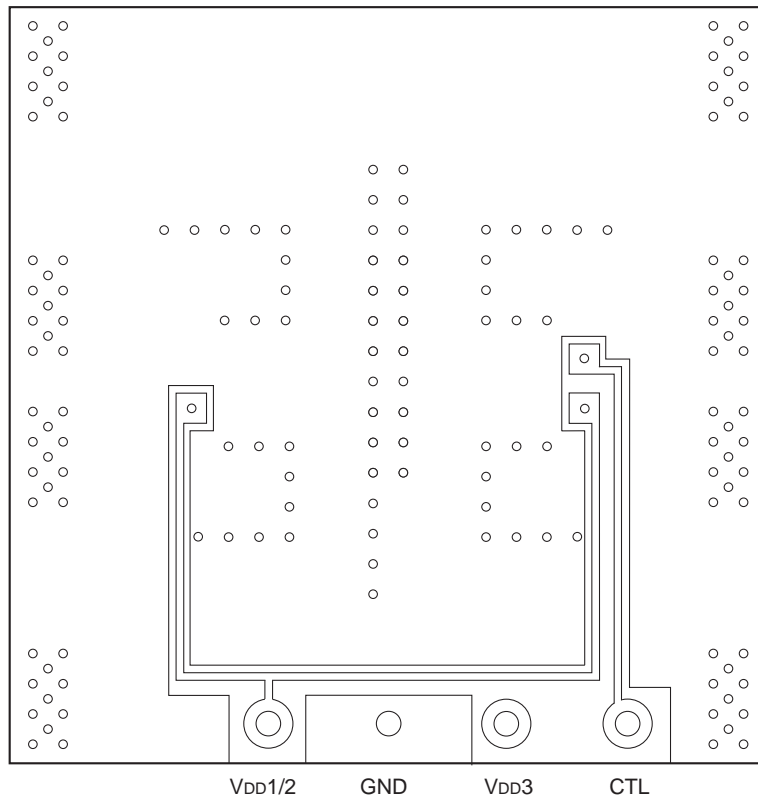
Example of Characteristics for Option Resistance R1 Changed (Ta = 25°C)



Recommended Evaluation Board



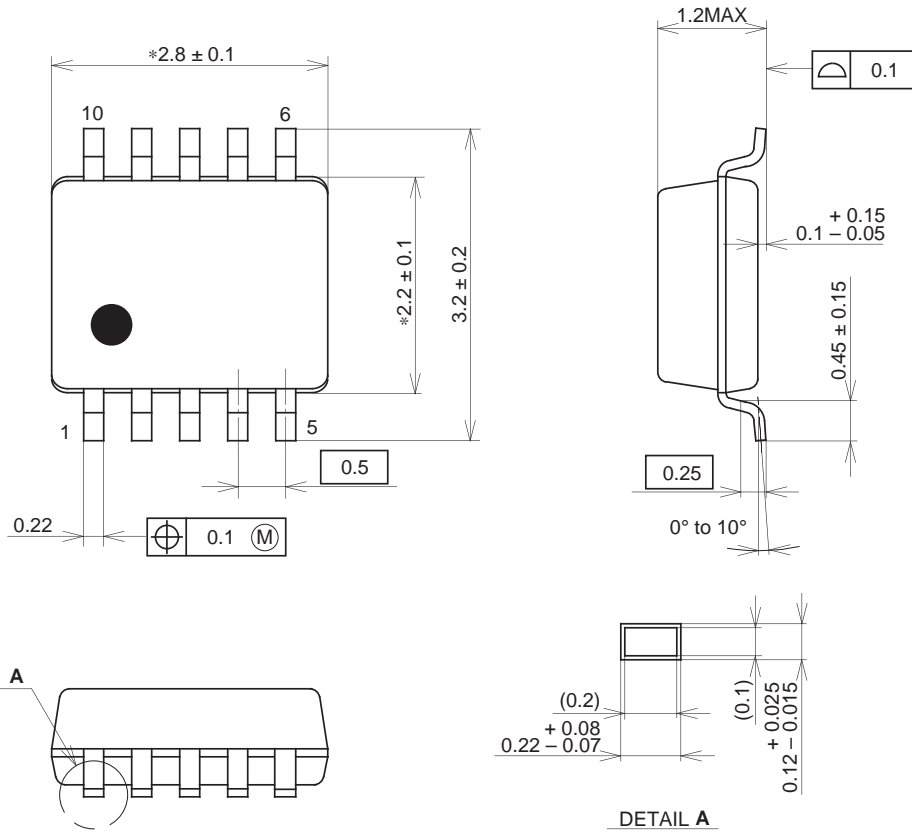
Back



Glass fabric-base 4-layer epoxy board (thickness: 0.2mm × 2), total thickness: 0.8mm  
 GND for the whole 2nd and 3rd layers

Package Outline Unit: mm

10PIN TSSOP(PLASTIC)



NOTE: "\*" Dimensions do not include mold protrusion.

PACKAGE STRUCTURE

SONY CODE	TSSOP-10P-L01
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.02g